

ABSTRACT

On the surface of a substrate 1, a precursory buffer layer 2' composed of an In-base compound or a Zn-base compound, not contained in the substrate 1, is formed so as to be stacked thereon as a polycrystal layer or an amorphous layer. Before a light emitting region is formed, the precursory buffer layer 2' is annealed for re-crystallization to thereby convert it into a buffer layer 2. This successfully provides a Zn-base semiconductor light emitting device which can readily be fabricated and capable of improving quality of the light emitting region, and a method of fabricating the same.